

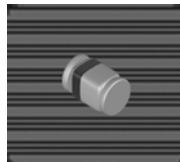


MCL4151

Fast Switching Diode

Features

- Silicon Epitaxial Planar Diodes
- Electrical data identical with the device 1N4151
- Micro MELF package



Applications

- Extreme fast switches

Mechanical Data

- Case: MicroMELF Glass Case
- Weight: approx. 12.3 mg
- Cathode Band Color: Black

Absolute Maximum Ratings

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Test Condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	75	V
Reverse voltage		V_R	50	V
Peak forward surge current	$t_p=1 \mu s$	I_{FSM}	2	A
Repetitive peak forward current		I_{FRM}	450	mA
Forward current		I_F	200	mA
Average forward current	$V_R=0$	I_{FAV}	150	mA
Power dissipation		P_V	500	mW

Thermal Characteristics

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Test Condition	Symbol	Value	Unit
Junction ambient	mounted on epoxy-glass hard tissue, Fig 4. 35 μm copper clad, $0.9m^2$ copper area per electrode	R_{thJA}	500	K/W
Junction temperature		T_J	175	$^{\circ}C$
Storage temperature range		T_{stg}	-65 to +175	$^{\circ}C$

Electrical Characteristics

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F=50mA$	V_F		0.88	1.0	V
Reverse current	$V_R=50V$	I_R			50	nA
	$V_R=50V, T_J=150^{\circ}C$				50	uA
Breakdown voltage	$I_R=5uA, t_p/T=0.01, t_p=0.3ms$	$V_{(BR)}$	75			V
Diode capacitance	$V_R=0, f=1MHz, V_{HE}=50mV$	C_D			2	pF
Reverse recovery time	$I_F=I_R=10mA, i_R=1mA$	t_{rr}			4	
	$I_F=10mA, V_R=6V, i_R=0.1 \times I_R, R_L=100\Omega$				2	nS

■Typical characteristics

($T_{amb} = 25^\circ\text{C}$ unless otherwise specified)

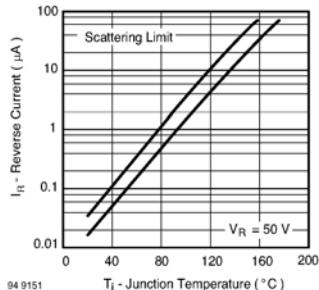


Fig. 1 Reverse Current vs. Junction Temperature

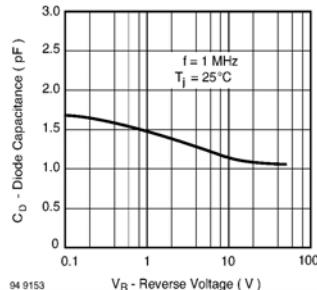


Fig. 3 Diode Capacitance vs. Reverse Voltage

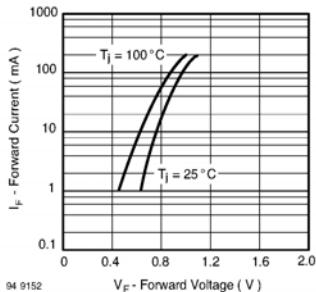


Fig. 2 Forward Current vs. Forward Voltage

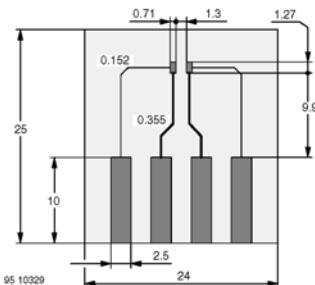


Fig. 4 Board for R_{thJA} definition (in mm)

Package Dimensions in mm (inches)

